

BULD125KC

NPN SILICON TRANSISTOR WITH INTEGRATED DIODE

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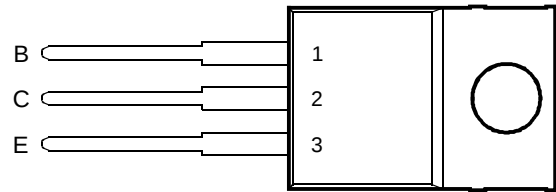
MAY 1994 - REVISED SEPTEMBER 1997

- **Designed Specifically for High Frequency Electronic Ballasts**
- **Integrated Fast t_{rr} Anti-Parallel Diode, Enhancing Reliability**
- **Diode t_{rr} Typically 1 μ s**
- **Tightly Controlled Transistor Storage Times**
- **Voltage Matched Integrated Transistor and Diode**
- **Characteristics Optimised for Cool Running**
- **Diode-Transistor Charge Coupling Minimised to Enhance Frequency Stability**

description

The new BULDxx range of transistors have been designed specifically for use in High Frequency Electronic Ballasts (HFEB's). This range of switching transistors has tightly controlled storage times and an integrated fast t_{rr} anti-parallel diode. The revolutionary design ensures that the diode has both fast forward and reverse recovery times, achieving the same performance as a discrete anti-parallel diode plus transistor. The integrated diode has minimal charge coupling with the transistor, increasing frequency stability, especially in lower power circuits where the circulating currents are low. By design, this new device offers a voltage matched integrated transistor and anti-parallel diode.

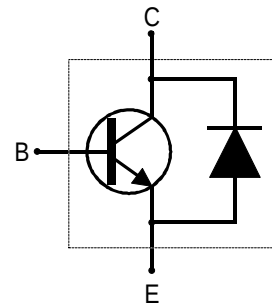
TO-220 PACKAGE
(TOP VIEW)



Pin 2 is in electrical contact with the mounting base.

MDTRACA

device symbol



absolute maximum ratings at 25°C case temperature (unless otherwise noted)

RATING	SYMBOL	VALUE	UNIT
Collector-emitter voltage ($V_{BE} = 0$)	V_{CES}	600	V
Collector-base voltage ($I_E = 0$)	V_{CBO}	600	V
Collector-emitter voltage ($I_B = 0$)	V_{CEO}	400	V
Emitter-base voltage	V_{EBO}	9	V
Continuous collector current	I_C	8	A
Peak collector current (see Note 1)	I_{CM}	12	A
Continuous base current	I_B	4	A
Peak base current (see Note 1)	I_{BM}	6	A
Continuous device dissipation at (or below) 25°C case temperature	P_{tot}	85	W
Maximum average continuous diode forward current at (or below) 25°C case temperature	$I_{E(av)}$	0.5	A
Operating junction temperature range	T_j	-65 to +150	°C
Storage temperature range	T_{stg}	-65 to +150	°C

NOTE 1: This value applies for $t_p = 10$ ms, duty cycle $\leq 2\%$.

PRODUCT INFORMATION

Information is current as of publication date. Products conform to specifications in accordance with the terms of Power Innovations standard warranty. Production processing does not necessarily include testing of all parameters.



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electrical characteristics at 25°C case temperature

PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
$V_{CEO(sus)}$ Collector-emitter sustaining voltage	$I_C = 0.1\text{ A}$ $L = 25\text{ mH}$	400			V
I_{CES} Collector-emitter cut-off current	$V_{CE} = 600\text{ V}$ $V_{BE} = 0$			10	μA
I_{EBO} Emitter cut-off current	$V_{EB} = 9\text{ V}$ $I_C = 0$			1	mA
$V_{BE(sat)}$ Base-emitter saturation voltage	$I_B = 0.3\text{ A}$ $I_C = 1.5\text{ A}$ (see Notes 2 and 3)		0.9	1.1	V
$V_{CE(sat)}$ Collector-emitter saturation voltage	$I_B = 0.3\text{ A}$ $I_C = 1.5\text{ A}$ $I_B = 0.6\text{ A}$ $I_C = 3\text{ A}$ (see Notes 2 and 3)		0.2 0.4	0.5 1	V
h_{FE} Forward current transfer ratio	$V_{CE} = 10\text{ V}$ $I_C = 0.01\text{ A}$ $V_{CE} = 1\text{ V}$ $I_C = 1.5\text{ A}$ (see Notes 2 and 3) $V_{CE} = 5\text{ V}$ $I_C = 3\text{ A}$	10 10 10	18 15 16	20 20	
V_{EC} Anti-parallel diode forward voltage	$I_E = 1\text{ A}$ (see Notes 2 and 3)		1.1	1.5	V

NOTES: 2. These parameters must be measured using pulse techniques, $t_p = 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$.

3. These parameters must be measured using voltage-sensing contacts, separate from the current carrying contacts, and located within 3.2 mm from the device body.

thermal characteristics

PARAMETER	MIN	TYP	MAX	UNIT
$R_{\theta JA}$ Junction to free air thermal resistance			62.5	$^{\circ}\text{C/W}$
$R_{\theta JC}$ Junction to case thermal resistance			1.47	$^{\circ}\text{C/W}$

switching characteristics at 25°C case temperature

PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
t_{rr} Anti-parallel diode reverse recovery time	Measured by holding transistor in an off condition, $V_{EB} = -3\text{ V}$. (see Note 4)		1		μs

NOTE 4: Tested in a typical High Frequency Electronic Ballast.

inductive-load switching characteristics at 25°C case temperature

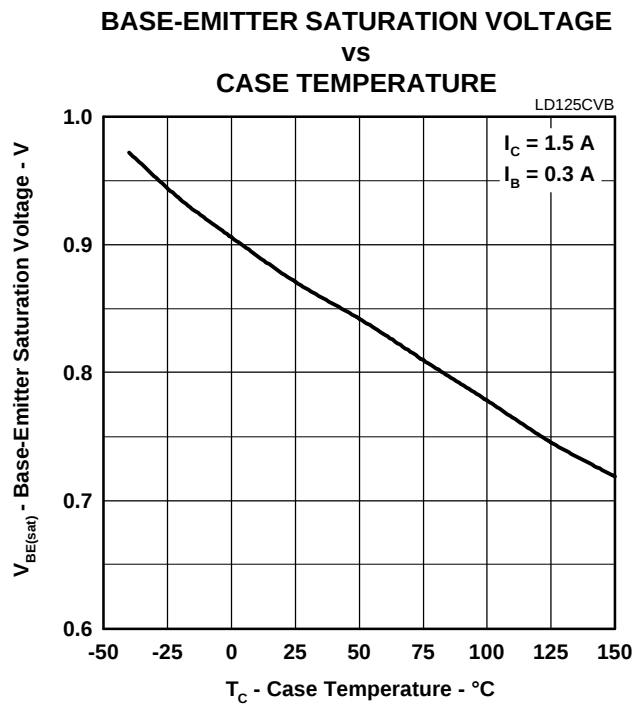
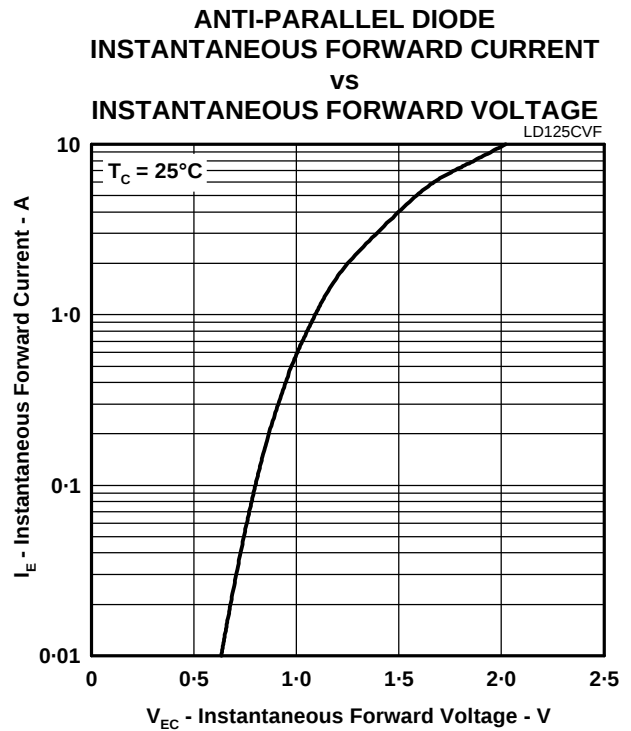
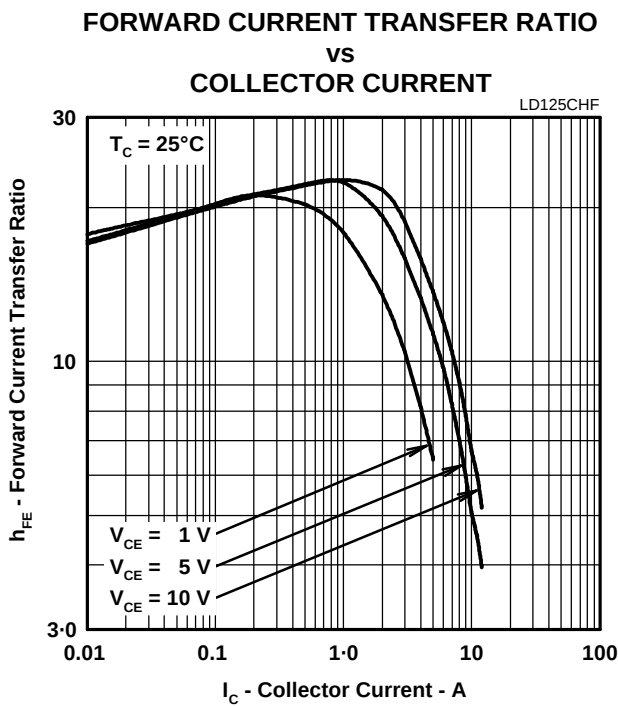
PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
t_{sv} Storage time	$I_C = 1.5\text{ A}$ $I_{B(on)} = 0.3\text{ A}$ $V_{CC} = 40\text{ V}$ $L = 1\text{ mH}$ $I_{B(off)} = 0.3\text{ A}$ $V_{CLAMP} = 300\text{ V}$		4	5	μs

resistive-load switching characteristics at 25°C case temperature

PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
t_{fi} Current fall time	$I_C = 1.5\text{ A}$ $I_{B(on)} = 0.3\text{ A}$ $V_{CC} = 300\text{ V}$ $I_{B(off)} = 0.3\text{ A}$		150	250	ns

PRODUCT INFORMATION

TYPICAL CHARACTERISTICS



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MAXIMUM SAFE OPERATING REGIONS

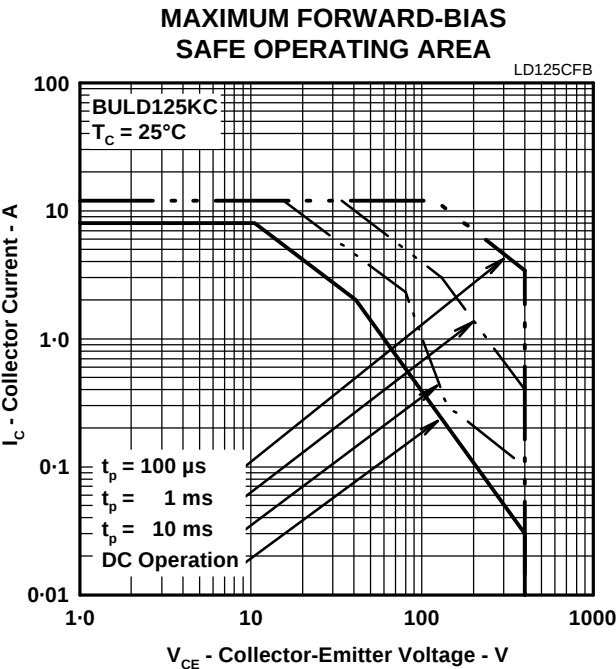


Figure 4.

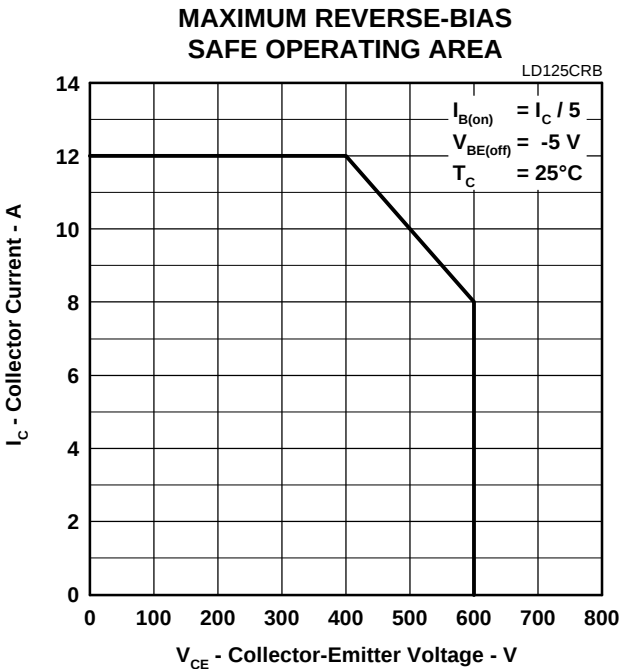


Figure 5.

THERMAL INFORMATION

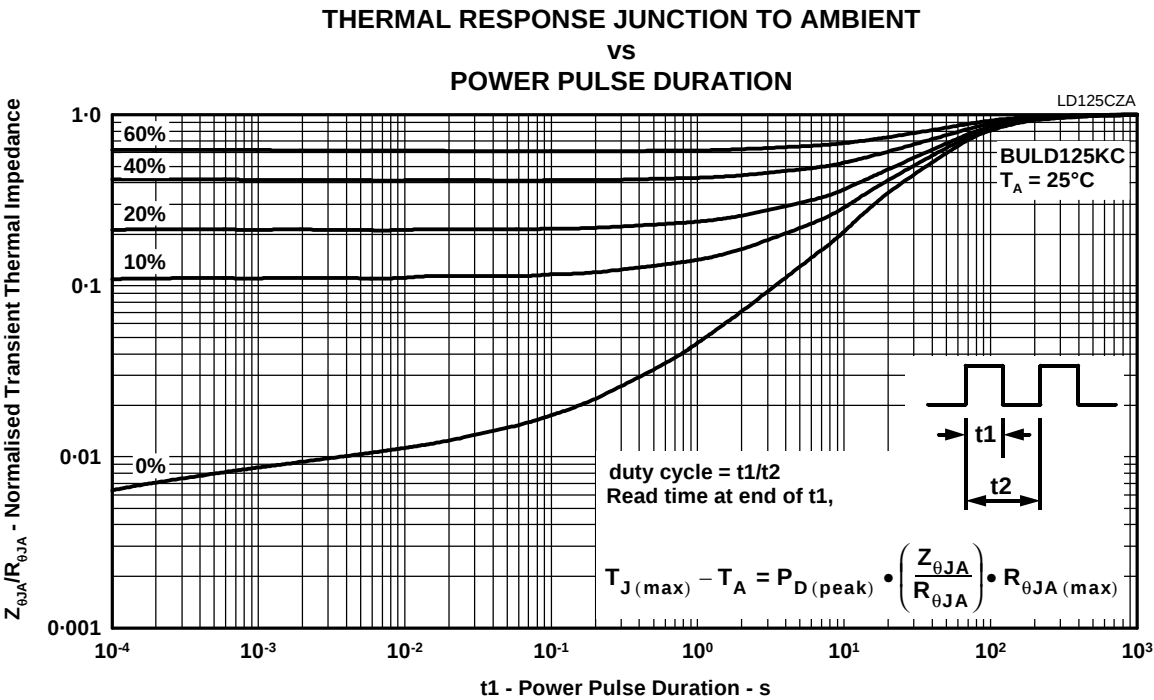


Figure 6.

PRODUCT INFORMATION

THERMAL INFORMATION

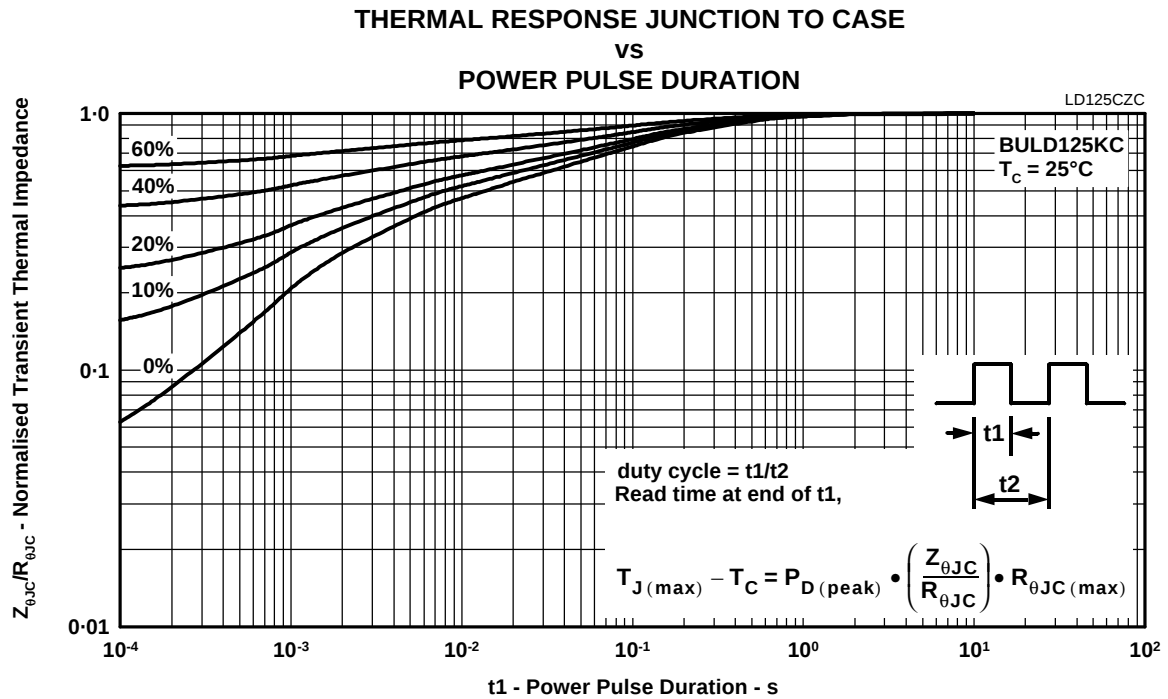


Figure 7.

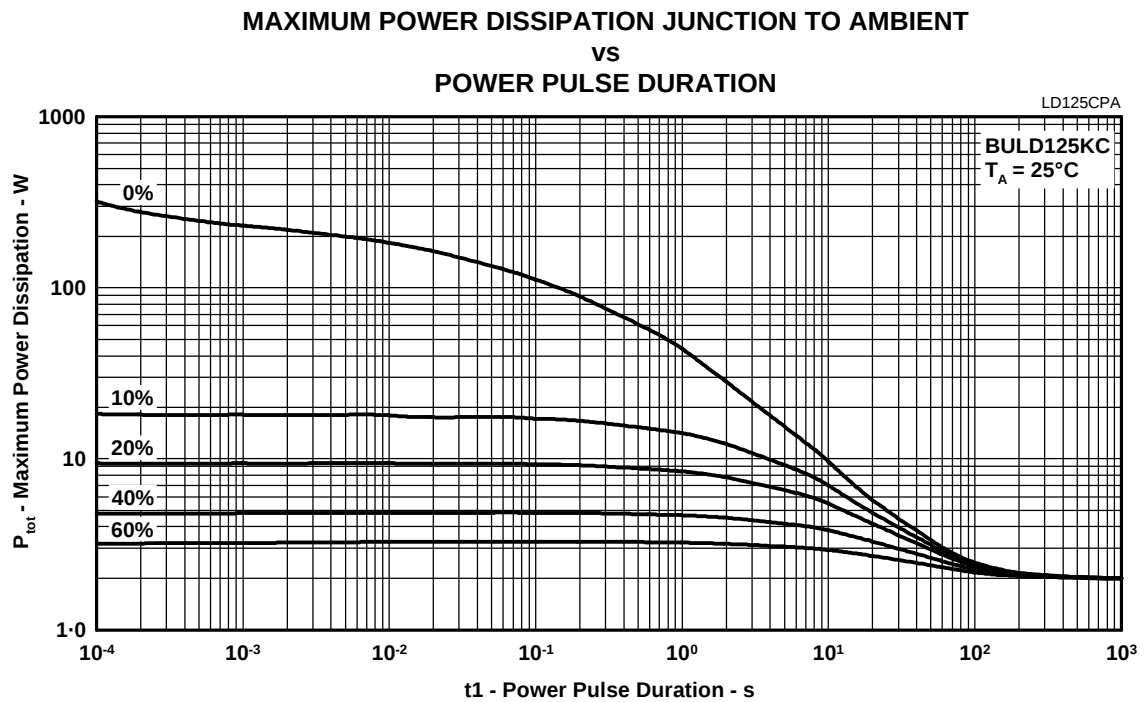
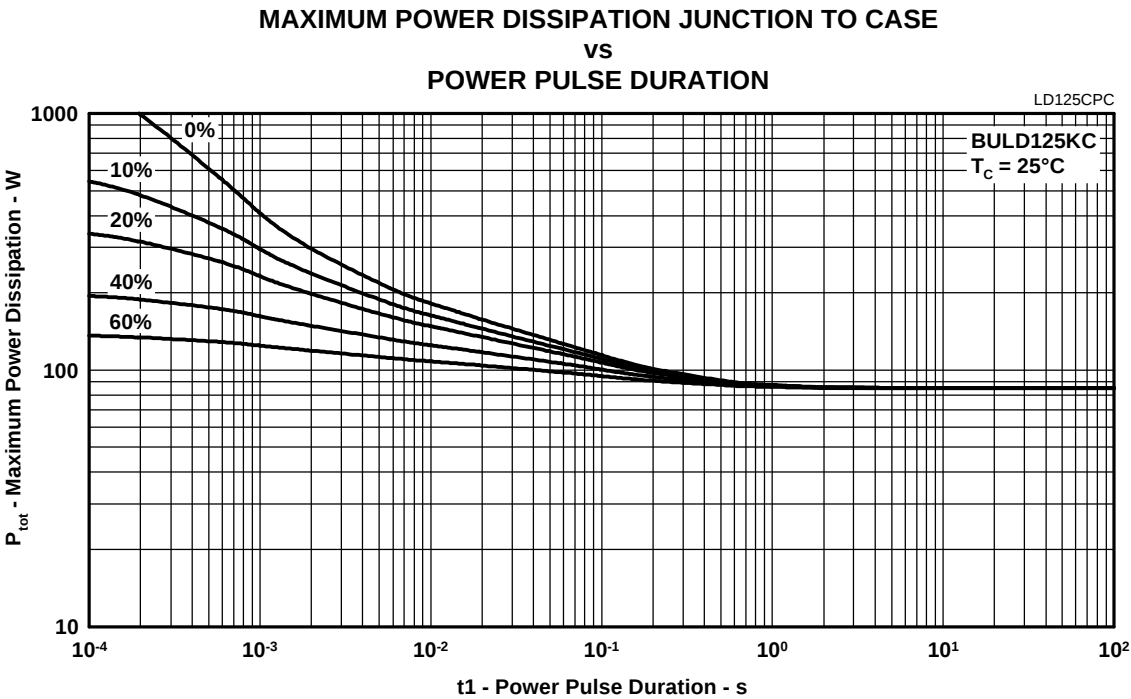


Figure 8.

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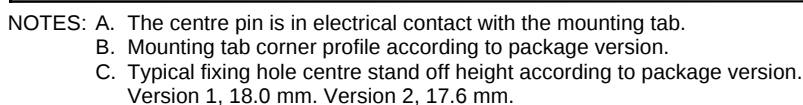
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THERMAL INFORMATION



TO-220

This single-in-line package consists of a circuit mounted on a lead frame and encapsulated within a plastic compound. The compound will withstand soldering temperature with no deformation, and circuit performance characteristics will remain stable when operated in high humidity conditions. Leads require no additional cleaning or processing when used in soldered assembly.



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